

Amendments to the Specification

Please add the following sentence below the title of the specification:

The present application is based on prior US application No. 10/102,505, filed on March 20, 2002, which is hereby incorporated by reference, and priority thereto for common subject matter is hereby claimed.

Please replace paragraph [0010] with the following amended paragraph. No new matter is introduced by this amendment.

[0010] Semiconductor device 1 is then thermally oxidized to simultaneously grow an extrinsic layer 23 of silicon dioxide on the sidewalls 19 of cavities 18, ~~which, formed having~~ ~~a~~ thermally grown silicon dioxide ~~which oxidizes the~~ sidewalls 19 of the cavities 18 ~~simultaneously adding silicon dioxide 23 to the sidewalls~~ and consumes a portion of sidewalls 19 to form an intrinsic layer 22 of silicon dioxide. A portion 24 of the cavities 18 is not filled with silicon dioxide. Between cavities 18, overlapping regions 26 of consumed portions or intrinsic layer 22 are formed. Although shown as two layers for the purposes of describing the invention, layer 22 and layer 23 constitute a homogeneous or single continuous layer. Note that the pillars 15 of semiconductor substrate material 10 are not consumed by the formation of intrinsic layer 22. Thus a ~~continuous~~ homogeneous or single continuous layer of silicon dioxide comprised of extrinsic layer 23 and intrinsic layer 22 is formed surrounding pillars 15 of semiconductor material. Since the oxidation rate of semiconductor

material is well established and easily controlled, the dimensions of the pillars 15 can be easily controlled.